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IDENTIFIER:

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TITLE:

Spin-on-glass etchback planarization process using an oxygen plasma to remove an etchback polymer residue

Detailed Description Text - DETX (10):

Second, the SOG layer 14 is partially etched (e.g., isotropic etched) and an accompanying polymer layer 18 also forms on the SOG layer surface as shown in FIG. 1. The polymer 18 can be formed during the etching back of the SOG layer with any fluorocarbon-type plasma, e.g., CH.sub.4, CHF.sub.3, C.sub.2F.sub.6, C.sub.3F.sub.8, etc. The polymer layer is formed thicker in the center of the substrate than in the outer periphery by the normal reaction kinetics.